

Erratum

Electrostatic gating of hybrid halide perovskite field-effect transistors: balanced ambipolar transport at room-temperature – ERRATUM

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In Mei et al.¹, the authors were initially published in the incorrect order:

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Correct order is, as listed:

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The publisher regrets the mistakes. The original article has been updated with the correct order of authors.

Reference

1. Y. Mei, C. Zhang, Z.V. Vardeny, and O.D. Jurchescu: Electrostatic gating of hybrid halide perovskite field-effect transistors: balanced ambipolar transport at room-temperature. *MRS Communications* (2015). doi: 10.1557/mrc.2015.21.

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